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FIG.1

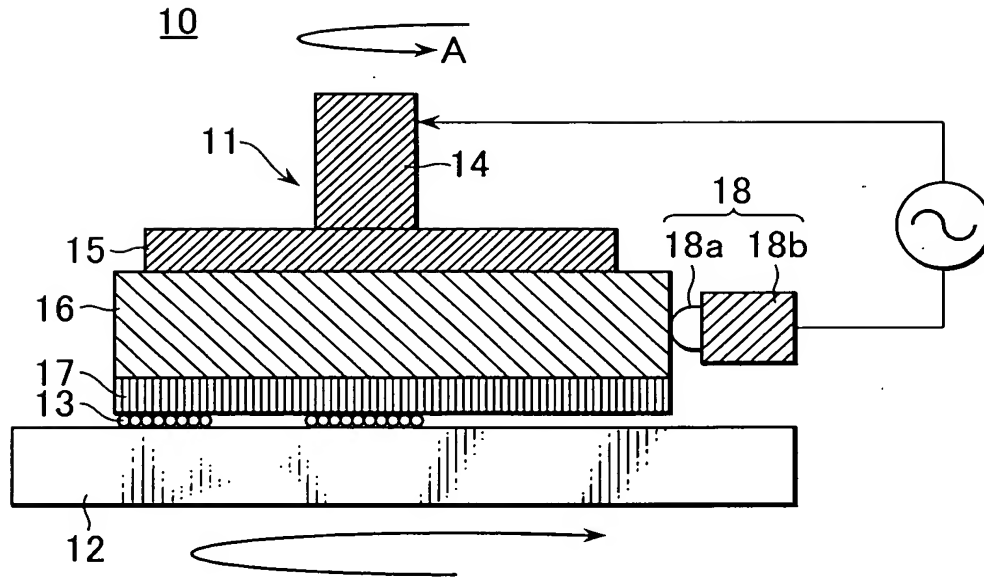
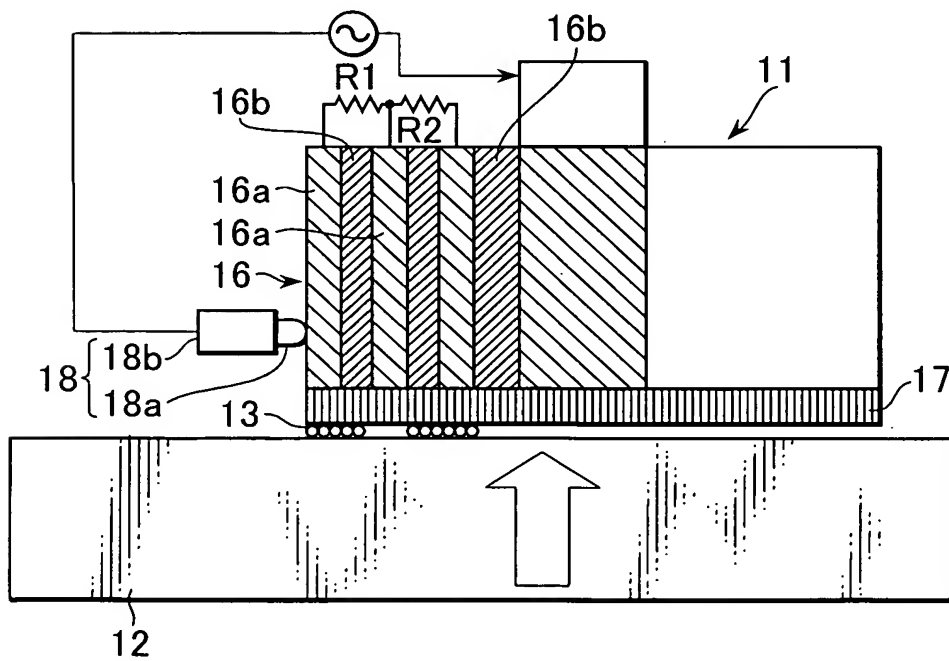


FIG.2



A cross-sectional view of a circular structure, labeled 16. It consists of a central core (16a) surrounded by multiple concentric layers (16b).

A cross-sectional view of a semiconductor device 11. The device is built on a substrate 12. A base layer 13 is formed on the substrate. A series of stacked layers 14, 16a, 16b, 18a, and 18b are formed on the base layer. A signal input 17 is shown on the right. A series of small circles 18 are shown at the bottom of the stack.

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FIG.5

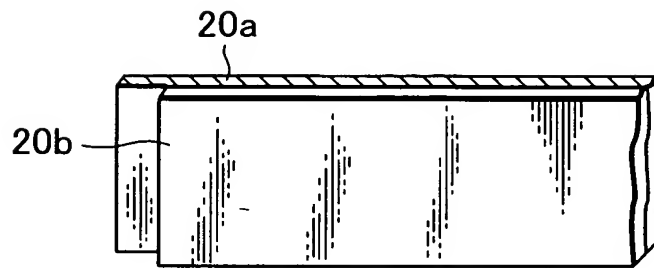


FIG.6

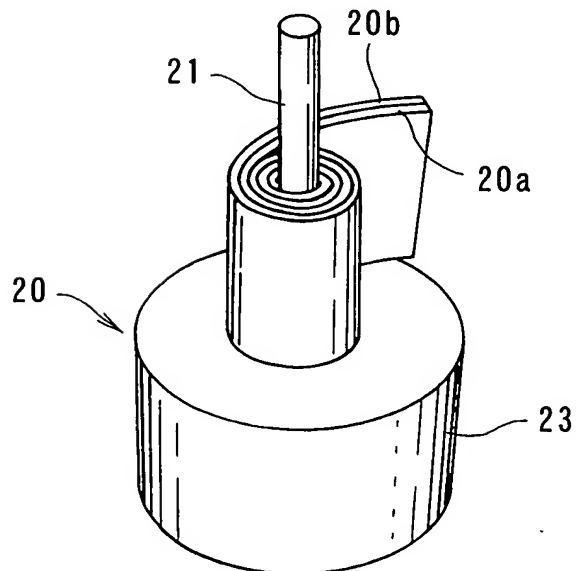


FIG.7

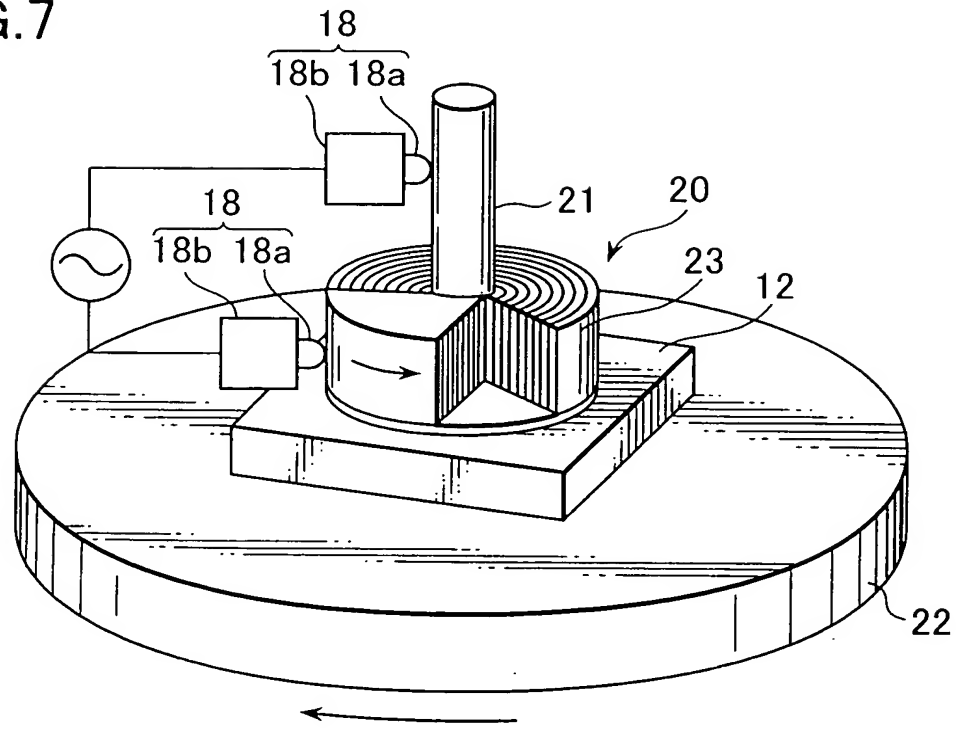
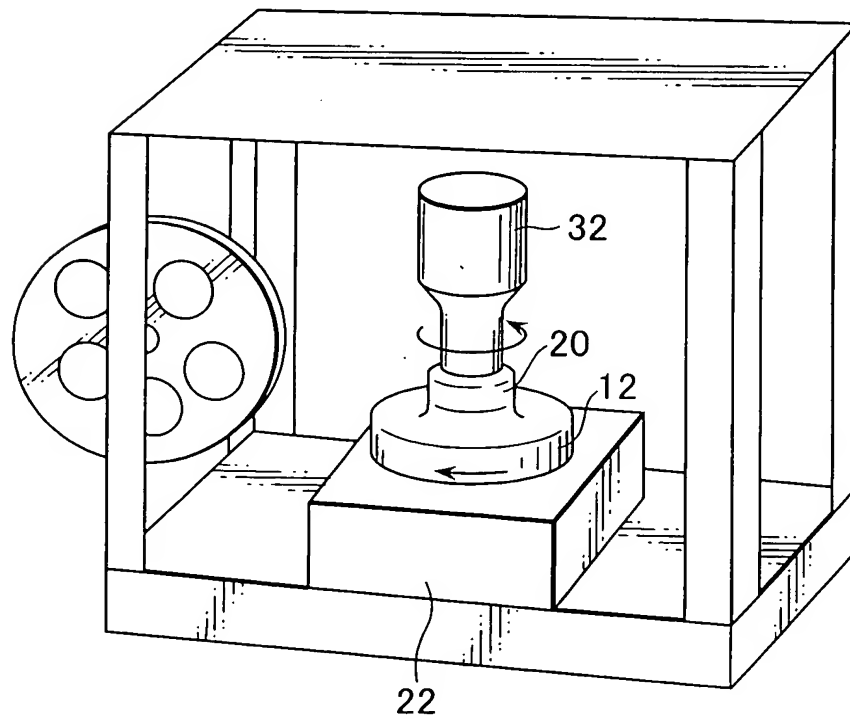


FIG.8



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FIG.9(a)

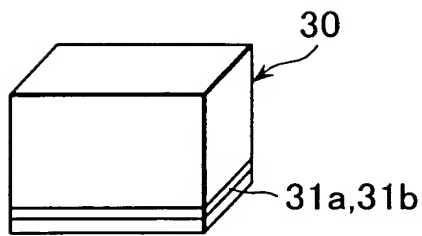


FIG.9(b)

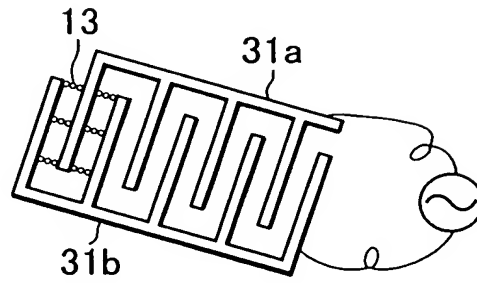


FIG.10

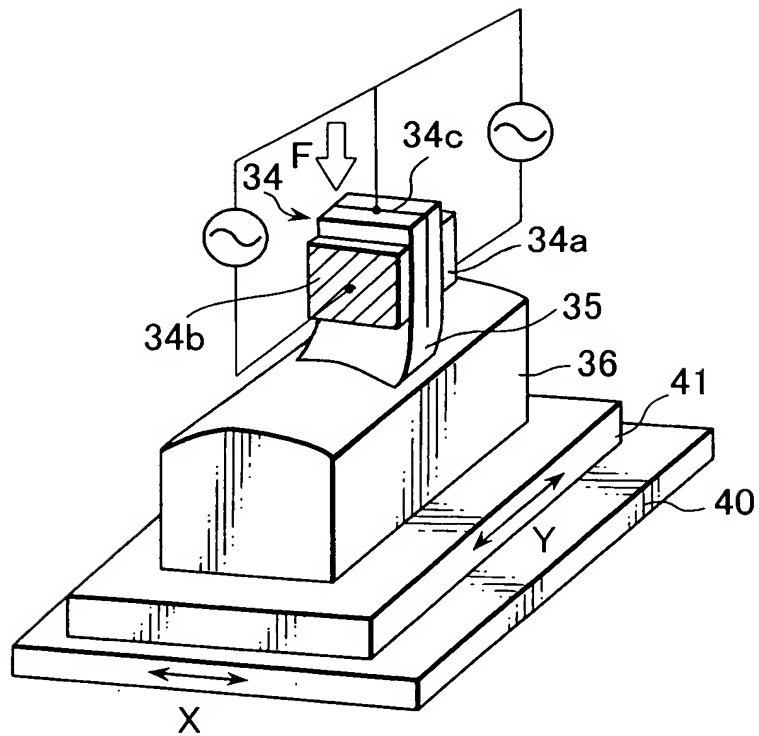


FIG.11

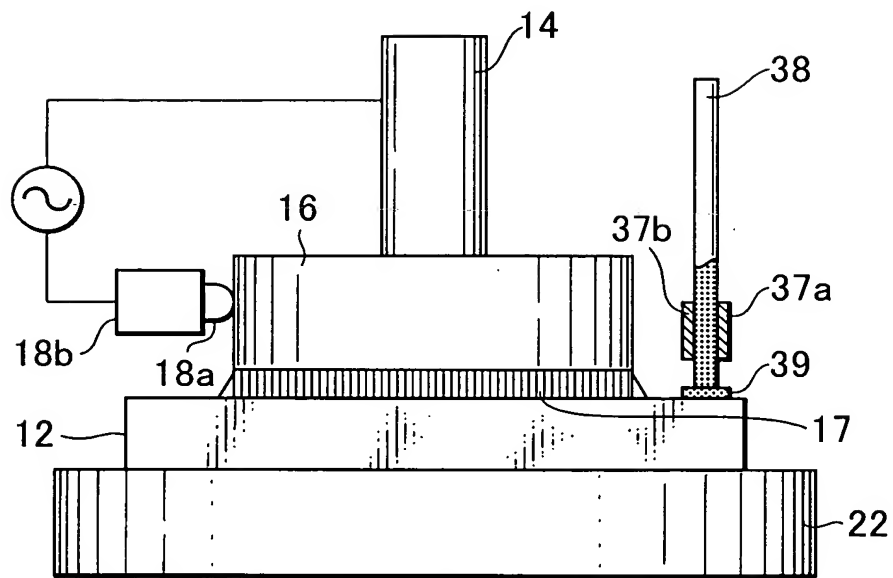


FIG.12
PRIOR ART

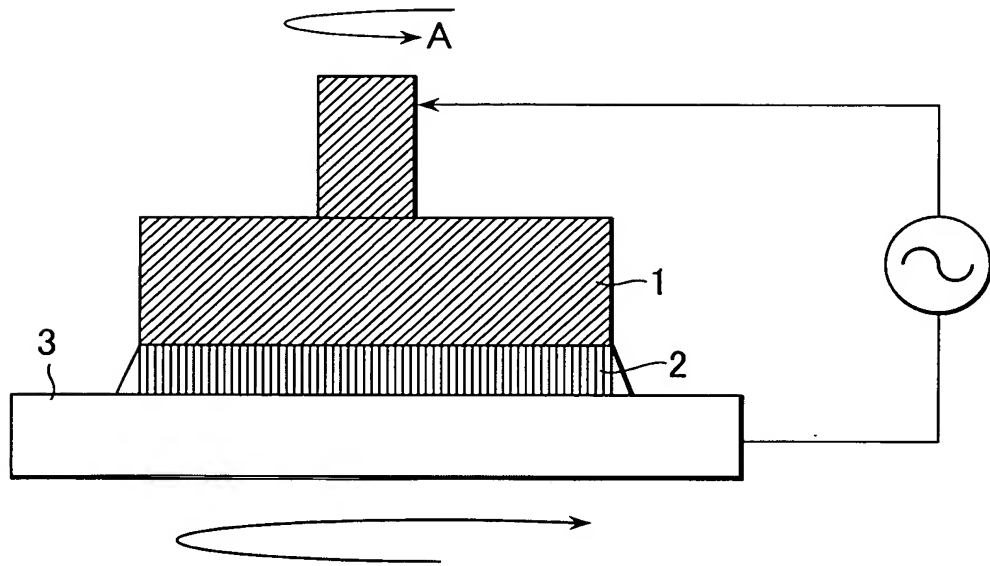


FIG.13
PRIOR ART

